

## Dual P-Channel 1.8-V (G-S) MOSFET

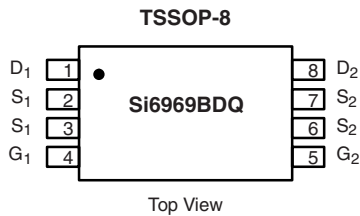
PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
- 12	0.030 at $V_{GS} = - 4.5$ V	- 4.6
	0.040 at $V_{GS} = - 2.5$ V	- 3.8
	0.055 at $V_{GS} = - 1.8$ V	- 3.0

### FEATURES

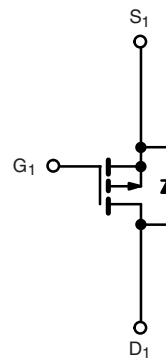
- Halogen-free Option Available
- TrenchFET<sup>®</sup> Power MOSFETs



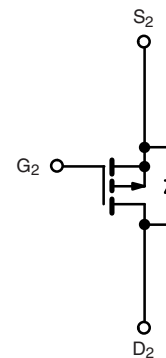
**RoHS\***  
COMPLIANT



Ordering Information: Si6969BDQ-T1  
Si6969BDQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	- 12		V	
Gate-Source Voltage	$V_{GS}$	$\pm 8$			
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	- 4.6	- 4.0	A
		$T_A = 70$ °C	- 3.8	- 3.2	
Pulsed Drain Current (10 $\mu$ s Pulse Width)	$I_{DM}$	- 30			
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	- 1.0	- 0.7		
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	1.14	0.83	W
		$T_A = 70$ °C	0.73	0.53	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ s	88	110	°C/W
		Steady State	120	150	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	65	80		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.



SPECIFICATIONS $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.45		-0.8	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 8\ \text{V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -9.6\ \text{V}, V_{GS} = 0\ \text{V}$			-1	$\mu\text{A}$
		$V_{DS} = -9.6\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 70^\circ\text{C}$			-25	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 8\ \text{V}, V_{GS} = -4.5\ \text{V}$	-30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\ \text{V}, I_D = -4.6\ \text{A}$		0.024	0.030	$\Omega$
		$V_{GS} = -2.5\ \text{V}, I_D = -3.8\ \text{A}$		0.031	0.040	
		$V_{GS} = -1.8\ \text{V}, I_D = -3.0\ \text{A}$		0.044	0.055	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -8\ \text{V}, I_D = -4.6\ \text{A}$		18		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -1.25\ \text{A}, V_{GS} = 0\ \text{V}$		-0.68	-1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -6\ \text{V}, V_{GS} = -4.5\ \text{V}, I_D = -4.6\ \text{A}$		16.5	25	nC
Gate-Source Charge	$Q_{gs}$		2			
Gate-Drain Charge	$Q_{gd}$		4.7			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\ \text{V}, R_L = 6\ \Omega$ $I_D \equiv -1.0\ \text{A}, V_{GEN} = -4.5\ \text{V}, R_G = 6\ \Omega$		20	40	ns
Rise Time	$t_r$		35	60		
Turn-Off Delay Time	$t_{d(off)}$		110	180		
Fall Time	$t_f$		90	150		
Source-Drain Reverse Recovery Time	$t_{rr}$		$I_F = -1.25\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		100	

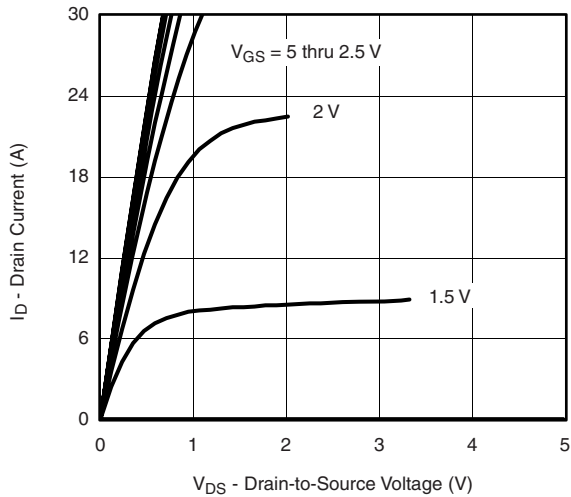
Notes:

a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

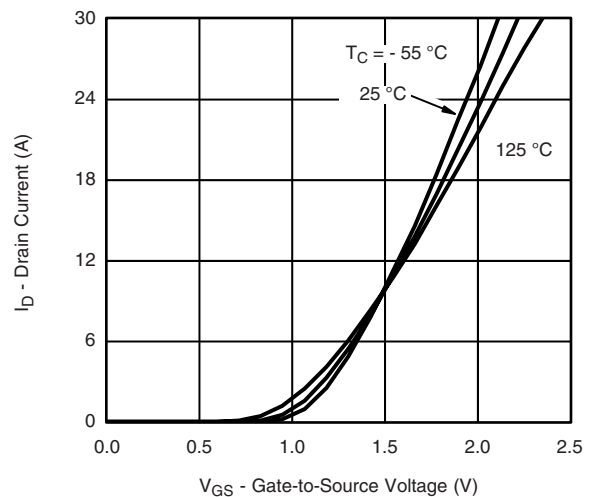
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS**  $25^\circ\text{C}$ , unless otherwise noted

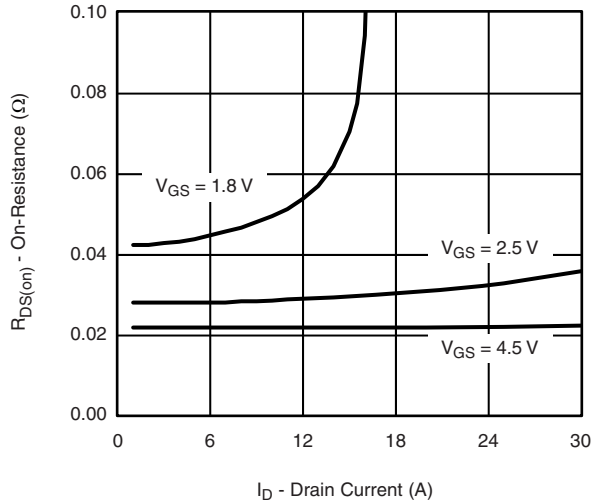


Output Characteristics

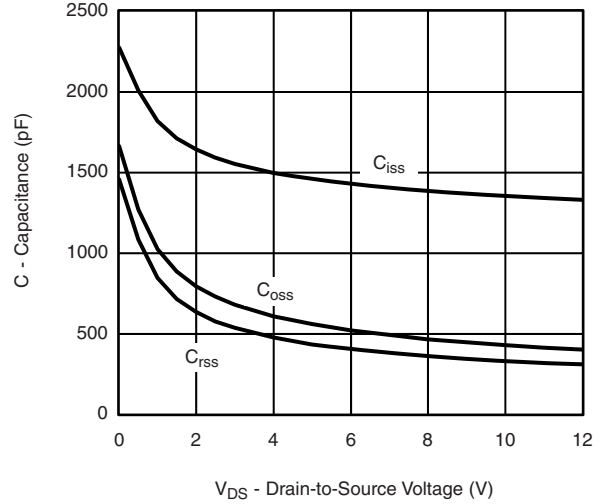


Transfer Characteristics

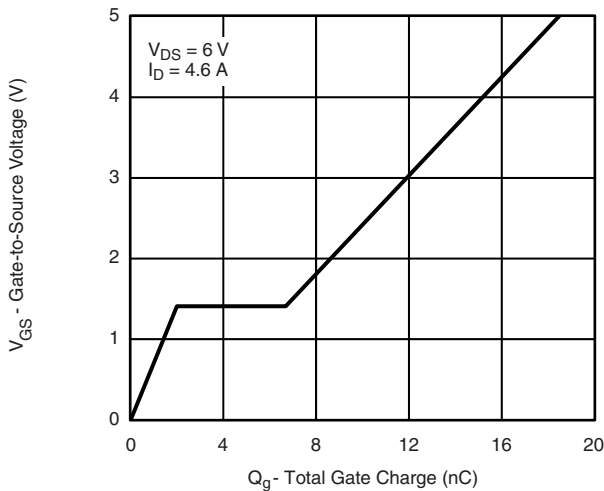
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



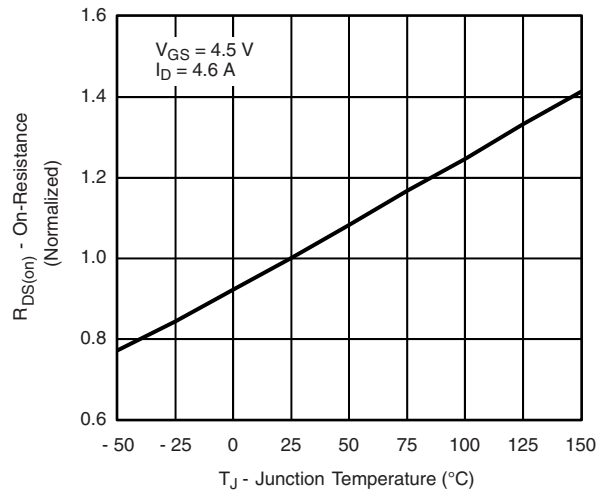
**On-Resistance vs. Drain Current**



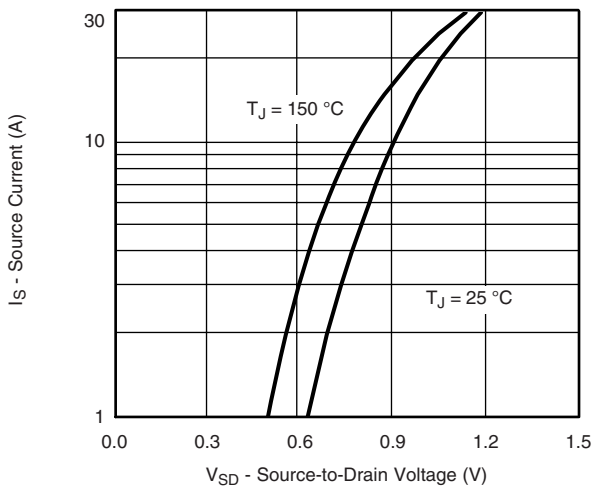
**Capacitance**



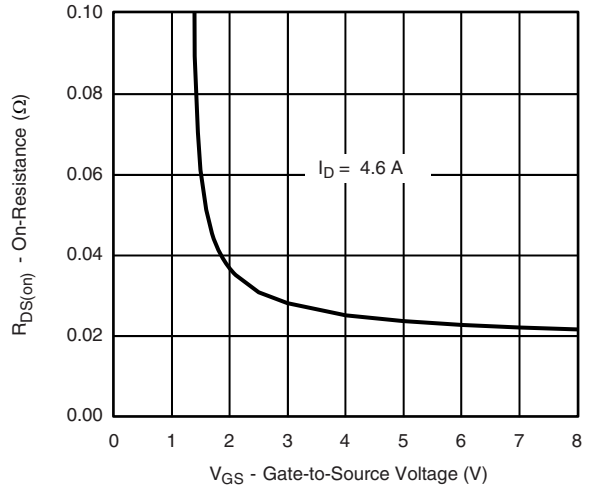
**Gate Charge**



**On-Resistance vs. Junction Temperature**

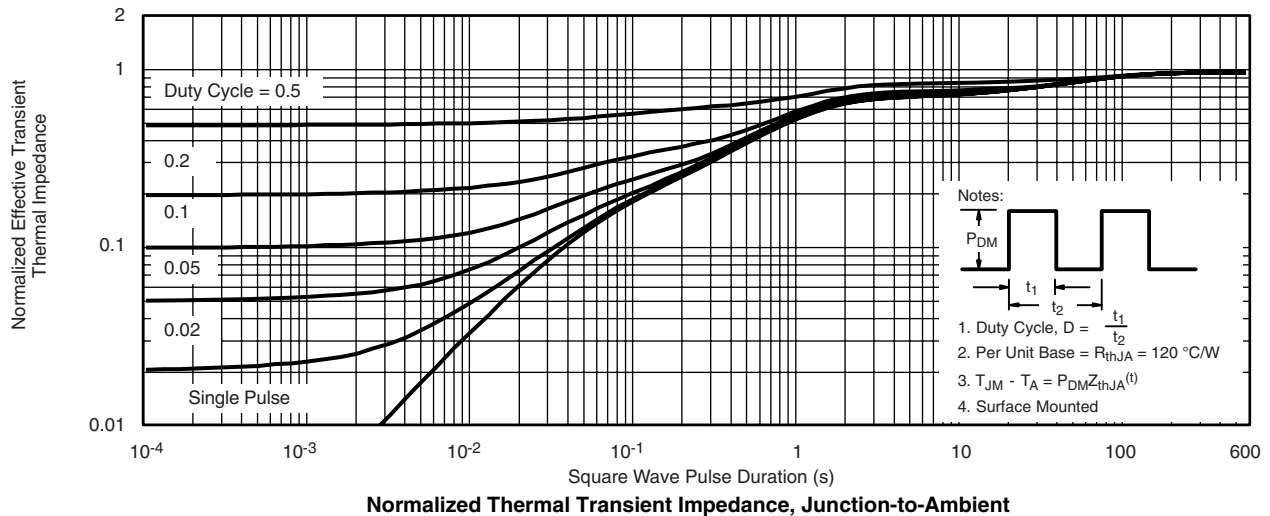
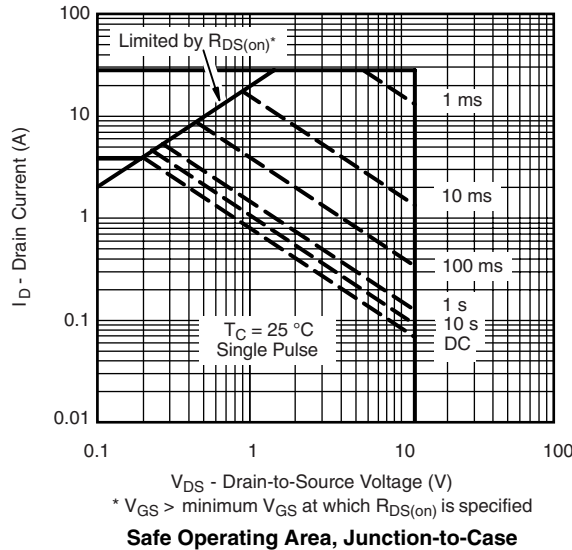
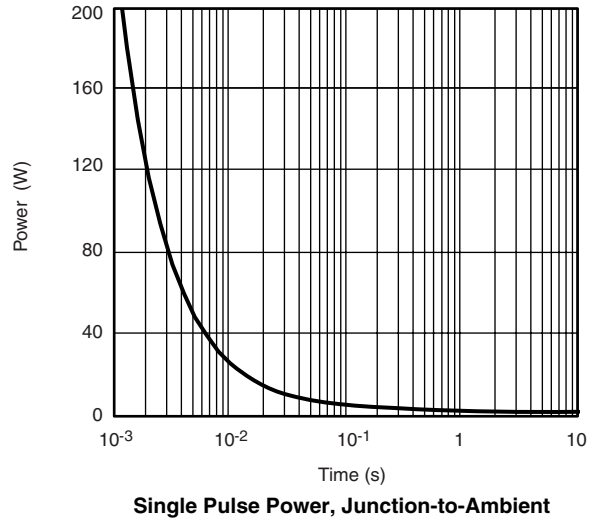
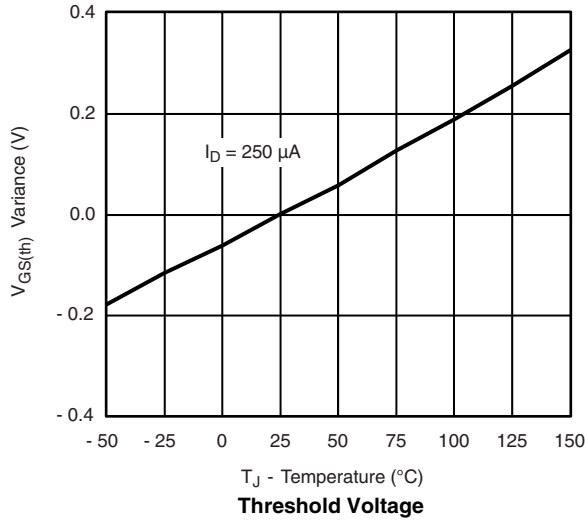


**Source-Drain Diode Forward Voltage**



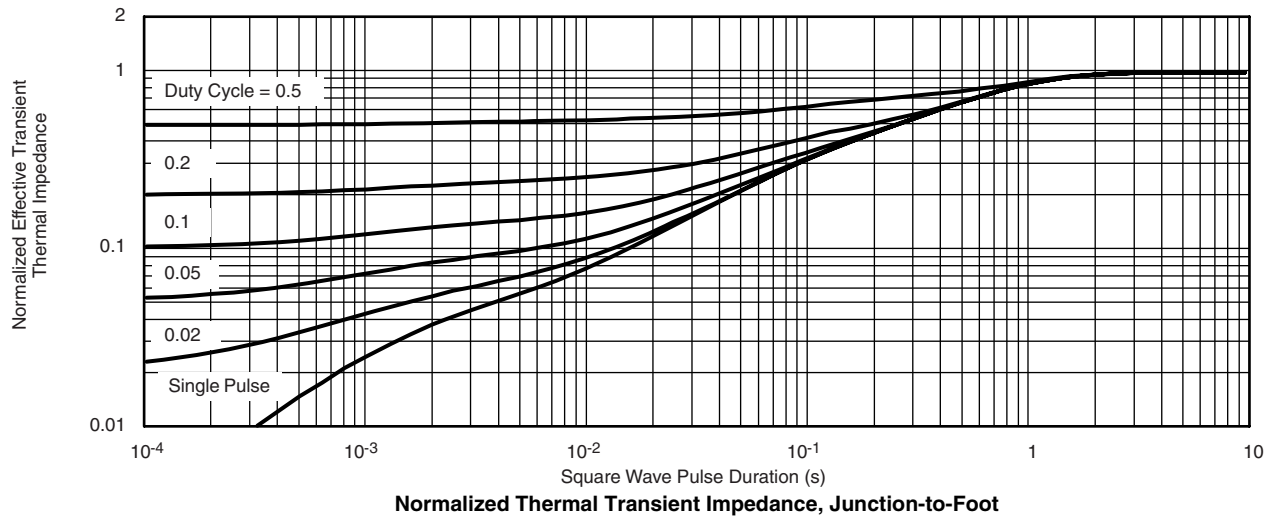
**On-Resistance vs. Gate-to-Source Voltage**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted





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